09/295607 Sheet_

Sheet 1 of 2

Form PTO-1449 U.S. Department of Commerce (Rev. 8-83) Patent and Trademark Office			Attorney D ck t No. 07	Serial No. N tY tAssign d					
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)			Applicant: Shunpel YAMAZAKI t al.						
			Filing Date:		Group: 2812				
	U.:	S. PATEN	T DOCUMENTS						
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appr priate)			
Loke	4,727,044	2/23/88	Yamazaki						
Loke	4,959,700	9/25/90	Yamazaki		y.				
Loke	5,142,344 8-25-19920	5/24/91	Yamazaki						
Loke	4,415,383	11/15/83	Naem et al.						
Like.	4,523,962	6/18/85	Nishimura						
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Loke.	5,306,651	4/26/94	Masumo et al.	437	40	5/10/91			
Loke	4,561,906	12/31/85	Calder et al.	437	101	10/24/83			
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Loke	59-121876	7/14/84	Japan		-	Abstract	L		
Loke	60-245174	12/4/85	Japan			Abstract			
Loke	6-59280	3/4/94	Japan			Abstract			
Loke	5-206468	8/13/93	Japan			Abstract	L		
Loke	1-187983	7/27/89	Japan			Abstract			
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Loke	Core at al. "High Performance TET's Exhibitated by YoCl Evaluar Lagar Annealing of								
Examine	Loke		Dat Considered		7/29/99				
*EXAMIN through o	ER: Initial if citation consid red, we citation if not in conformance and reant.	h therorno not consid	ot citation is in confe red. Includ copy of	ormance v this form	with MPEP 6 with n xt c	09; Draw lin ommunicati	e n		

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F rm PTO-1449	U.S. Department of Commerce		Attorney Docket No. 0756-1961		Senal No. 09/295,607			
(Rev. 8-83) Patent and Trademark Office INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)			Applicant: Shunpei YAMAZAKI et al.					
			Filing Date: April 22, 1	Group: 2811				
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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Dat		
Loke	5,147,826	09/15/92	Liu et al		4			
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Loke	EP 0 474 289 A1	03/11/92	Europe					
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V	62-188373	08/17/87	Japan			Abstract	L	
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	Crowder et al., "DMOS FET with Common Field and Channel Doping", IBM Technical Disclosure Bulletin, Vol. 20, No. 4, September 1977, pp. 1617-1621							
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*EXAMINER: Initial if citation considered, whether in not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Submitted with 1DS of September 5, 2000

Form PTO-	1449	U.S.Department of Commerce	Atty Docket 0756-1961		Serial No. 09/295,607		
(Rev. 8-83)	FORMATION DISCLO	Patent and Trademark Office	Applicants: Shunpei YAMAZAKI et al.				
· ·	13	SURE STATEMENT	Applicants: Ondipor 17.	WIAZAKI C	r an.		
MAY 1 6	2002		Filing Date: April 22, 199)9	Group Art Unit: 2811		
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Initial						Yes	No
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	02-153896		JP			Eng Abst	L
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	04-133029		JP BEST AVA	LADE	, •	Eng Abst	L
	04-186775		JP .			Eng Abst	
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Examiner		•		7/27/0			

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